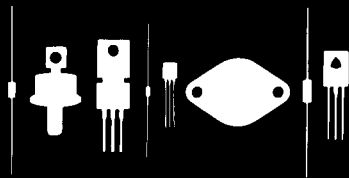


Central Semiconductor Corp.
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 145 Adams Avenue
 Hauppauge, New York 11788



2N404A

GERMANIUM TRANSISTOR

JEDEC TO - 5 CASE

(all leads insulated from case)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N404A is a Germanium PNP Transistor designed for low frequency medium power amplifier and swithcing applications.

MAXIMUM RATINGS (T_A = 25° C)

Collector-Base Voltage	V _{CB0}	40 volts
Collector-Emitter Voltage (Punch - through)	V _{pt}	35 volts
Emitter-Base Voltage	V _{EB0}	25 volts
Collector Current	I _C	150 m Amps
Emitter Current	I _E	150 m Amps
Power Dissipation	P _T	150 m Watts
Operating Junction Temperature	T _j	-65 to 100° C
Storage Temperature	T _{stg}	-65 to 100° C

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

<u>Symbol</u>	<u>Test Conditions</u>	<u>Min.</u>	<u>Max.</u>	<u>Unit</u>
I _{CB0}	V _{CB} = 12 V		5	uA
I _{CB0}	V _{CB} = 12V, T _A = 80° C		90	uA
I _{EBO}	V _{EB} = 2.5V		2.5	uA
V _{CB0}	I _C = 20 uA	40		V
V _{EBO}	I _E = 20 uA	25		V
V _{CE} (s)	I _C = 12 mA, I _B = 0.4 mA		0.15	V
V _{CE} (s)	I _C = 24 mA, I _B = 1.0 mA		0.20	V
V _{BE} (s)	I _C = 12 mA, I _B = 0.4 mA		0.35	V
V _{BE} (s)	I _C = 24 mA, I _B = 1.0 mA		0.40	v
h _{FE}	V _{CE} = 0.15V, I _C = 12 mA	30		-
h _{FE}	V _{CE} = 0.20V, I _C = 24 mA	24		-
V _{EBfL}	V _{CB} = 35V		1.0	V
h _{fe}	V _{CE} = 6V, I _C = 1 mA, f = 1 Khz	135 typ.		-
h _{ie}	V _{CE} = 6V, I _C = 1 mA, f = 1 Khz	4 typ.		Kohm
h _{oe}	V _{CE} = 6V, I _C = 1 mA, f = 1 Khz	50 typ.		umhD
h _{re}	V _{CE} = 6V, I _C = 1 mA, f = 1 Khz	7X10 ⁻⁴ typ.		-
c _{ob}	V _{CB} = 6V, f = 2 mHZ		20	Pf
f _{hfb}	V _{CB} = 6V, I _E = 1 mA	4		mHZ